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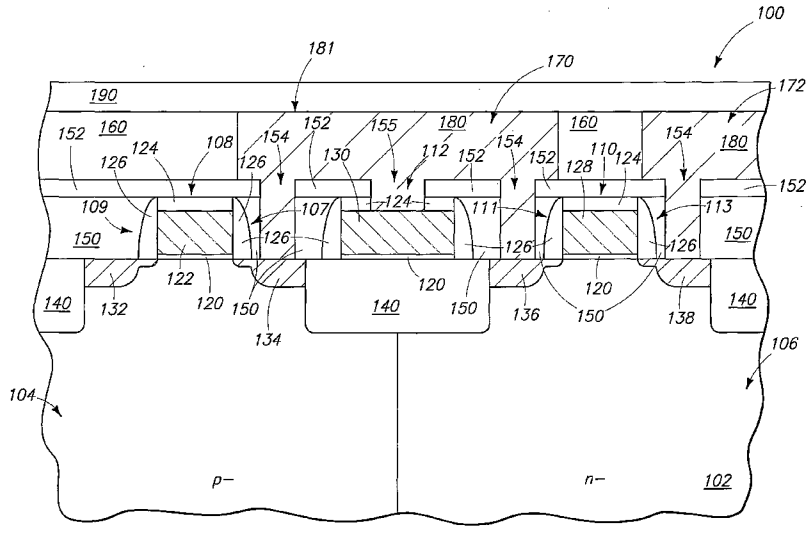
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(54) Title: METHODS OF FORMING ELECTRICAL CONNECTIONS FOR SEMICONDUCTOR CONSTRUCTIONS



(57) Abstract: The invention includes methods for forming electrical connections associated with semiconductor constructions. A semiconductor substrate is provided which has a conductive line thereover, and which has at least two diffusion regions adjacent the conductive line. A patterned etch stop is formed over the diffusion regions. The patterned etch stop has a pair of openings extending through it, with the openings being along a row substantially parallel to an axis of the line. An insulative material is formed over the etch stop. The insulative material is exposed to an etch to form a trench within the insulative material, and to extend the openings from the etch stop to the diffusion regions. At least a portion of the trench is directly over the openings and extends along the axis of the line. An electrically conductive material is formed within the openings and within the trench.

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